# Tuning the bandgap of double perovskites

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With great achievements in efficiency, stability, and large-scale preparation of perovskite solar cells (PSCs), the commercialization of PSC is ongoing, but there is still an issue on lead toxicity. Although lead content in the device is low, the water solubility of lead salts leads to potential environmental pollution. At present, the non-lead perovskites studied include: divalent metal perovskite (e.g., Sn<sup>2+</sup>, Ge<sup>2+</sup>, Cu<sup>2+</sup>), trivalent metal perovskite (e.g., Bi<sup>3+</sup>, Sb<sup>3+</sup>, In<sup>3+</sup>), tetravalent metal double perovskite (e.g., Sn4+, Pd4+, Ti4+, Pt4+) and monotrivalent mixed double perovskite (e.g., Ag<sup>+</sup> and Bi<sup>3+</sup>, Ag<sup>+</sup> and In<sup>3+</sup>, Ag<sup>+</sup> and Sb<sup>3+</sup>). Their properties are summarized in Table 1. Since the first report on non-lead double perovskite Cs<sub>2</sub>AgBiBr<sub>6</sub> in 2016<sup>[1]</sup>, this material has caused extensive research in optoelectronic devices because of its long carrier lifetime<sup>[1]</sup> and good stability<sup>[2]</sup>. However, owing to its wide and indirect bandgap ( $E_{\alpha}$ ) (~2.0 eV), its light absorption range is narrow, which limits its application in photovoltaics. At present, the power conversion efficiency (PCE) of Cs<sub>2</sub>AgBiBr<sub>6</sub> device is  $\sim 3\%^{[3]}$ . To enhance PCE, the  $E_q$  needs to be narrowed. The efforts in this area focus on adjusting chemical composition and physical structure (Fig. 1) to tune  $E_{q}$ .

A common attempt to tune the  $E_{q}$  of double perovskite is to adjust the chemical composition of compound  $A_2B(I)B(III)X_6$ .

A-site. Doping alkali metal ions like Rb<sup>+</sup>, K<sup>+</sup>, and Na<sup>+</sup> made little effect on  $E_{q}^{[4]}$ . Chen *et al.*<sup>[5]</sup> introduced Rb<sup>+</sup> into Cs<sub>2</sub>AgBiBr<sub>6</sub> to form (Cs<sub>1-x</sub>Rb<sub>x</sub>)<sub>2</sub>AgBiBr<sub>6</sub> and effectively passivated the defects of double perovskite, thus increasing PCE to 1.5%. But this doping could not significantly change the  $E_{\alpha}$ . When doping A-site to change the dimension of perovskite from 3D to 2D, the  $E_{\alpha}$  and electronic structure can be tuned. In 2019, Mitzi et al.<sup>[6]</sup> reported that a stable 2D double perovskite [AE2T]<sub>2</sub>AgBil<sub>8</sub> was formed by using multifunctional organic molecules with a direct  $E_q$  of 2.01 eV.

**X-site.** For lead-based perovskites, the  $E_q$  decreases with the increasing of halogen atom radius, and similar results are also observed in double perovskites. The introduction of Cl<sup>-</sup> can greatly increase  $E_{q}$ , while l<sup>-</sup> doping can significantly reduce  $E_{g}$ , which is 2.77 eV (X = Cl), 1.95 eV (X = Br), and 1.75 eV (X = I) for  $Cs_2AgBiX_6^{[7]}$ . When X site is I, the stability for double perovskite decreases. It is difficult to prepare

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Cs<sub>2</sub>AgBil<sub>6</sub> experimentally, because the formation energy of  $Cs_3Bi_2I_9$  is lower. As reported by Ma et al.<sup>[8]</sup>, the  $E_q$  of Cs<sub>2</sub>NaBil<sub>6</sub> was relatively narrow (1.66 eV), but it can easily decompose into Cs<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>, yielding a 0.42% PCE.

B-site. The structure of double perovskite consists of B(I)X<sub>6</sub> and B(III)X<sub>6</sub> with alternating octahedrons connected by vertices. Substituting B-site elements can tune Eq. Karunadasa et al.<sup>[9]</sup> found that doping low content of toxic TI (TI+, TI<sup>3+</sup>) into Cs<sub>2</sub>AgBiBr<sub>6</sub> to form Cs<sub>2</sub>(Ag<sub>1-a</sub>Bi<sub>1-b</sub>)TI<sub>x</sub>Br<sub>6</sub> (0.003 < x =a + b < 0.075) can significantly reduce its  $E_q$  to 1.40 eV for Cs<sub>2</sub>(Ag<sub>1-a</sub>Bi<sub>1-b</sub>)Tl<sub>0.075</sub>Br<sub>6</sub>. Replacing Ag<sup>+</sup> and Bi<sup>3+</sup> by Tl<sup>+</sup>/Tl<sup>3+</sup> yielded defects, leading to band-edge reconstruction. Using unstable Sn<sup>2+</sup> (can be oxidized to Sn<sup>4+</sup>) to replace both Ag<sup>+</sup> and  $Bi^{3+}$  can also reduce  $E_{q}$  to 1.71 eV (indirect) and 1.48 eV (direct)<sup>[10]</sup>. These results indicate that the band-edge reconstruction caused by the lattice distortion due to B-site ion doping can tune the  $E_{q}$  of double perovskite. Mitzi *et al.*<sup>[11]</sup> reported that the use of trivalent metal In<sup>3+</sup> or Sb<sup>3+</sup> can also significantly tune  $E_{\alpha}$ , which could be increased to 2.4 eV by replacing 75% of Bi<sup>3+</sup> with In<sup>3+</sup>. While replacing 37.5% Bi<sup>3+</sup> with Sb<sup>3+</sup> could reduce  $E_q$  to 1.86 eV. When using In<sup>+</sup> to replace Aq<sup>+</sup>, it was predicted that the  $E_q$  of Cs<sub>2</sub>InBiCl<sub>6</sub> (1.02 eV) and Cs<sub>2</sub>InSbCl<sub>6</sub> (0.91 eV) would be very suitable for photovoltaics<sup>[12]</sup>. However, In<sup>+</sup> is extremely unstable and can be easily oxidized into In<sup>3+[13]</sup>.

When using  $Cu^+/Cu^{2+}$  to replace part of Ag<sup>+</sup> in Cs<sub>2</sub>Ag-BiBr<sub>6</sub>, there is no obvious effect on  $E_{a}^{[14]}$ . Cu<sup>+</sup> (ionic radius 77 pm, hereafter omit) and Cu<sup>2+</sup> (73 pm) are much smaller than Ag<sup>+</sup> (115 pm). They can cause lattice defects, and the absorption tail extends from 610 to 860 nm. This was due to the absorption of the defect intermediate state. Similarly, Fe<sup>3+</sup> (65 pm) was used to replace part of Bi<sup>3+</sup> (103 pm)<sup>[15]</sup>. Since the size of Fe<sup>3+</sup> is guite different from Bi<sup>3+</sup>, it can easily cause lattice distortion and defects. The lattice constant was reduced from 11.27 to 11.25 Å, and Cs<sub>2</sub>AgBi<sub>0.886</sub>Fe<sub>0.114</sub>Br<sub>6</sub> was obtained as a black crystal. Though E<sub>a</sub> did not change obviously, the light absorption was greatly increased by defects. Recently, Gao et al.[16] demonstrated that Fe<sup>3+</sup> could replace diamagnetic In<sup>3+</sup> to yield Cs<sub>2</sub>AgIn<sub>1-x</sub>Fe<sub>x</sub>Cl<sub>6</sub> and form [FeCl<sub>6</sub>]<sup>3-</sup>·[AgCl<sub>6</sub>]<sup>5-</sup> domains, and the connection of larger [FeCl<sub>6</sub>]<sup>3-,</sup>[AgCl<sub>6</sub>]<sup>5-</sup> domains leads to segregated Fe<sup>3+</sup>-rich phases. The E<sub>q</sub> of Cs<sub>2</sub>AgInCl<sub>6</sub> was tuned from 2.8 to 1.6 eV via Fe<sup>3+</sup>-alloying.

The second approach to tune  $E_{q}$  of double perovskite is to adjust the physical structure. First-principles calculations indicated that changing the order of Ag<sup>+</sup> and Bi<sup>3+</sup> in space can significantly reduce  $E_{q}$ . When the arrangement of Ag<sup>+</sup> and

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Table 1.	Pror	oerties	of le	ad-free	perovskites.
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Structure formula	Representative	Advantage	Disadvantage
AB(II)X <sub>3</sub>	FASnl <sub>3</sub>	High absorption, high mobility	Unstable
$A_2B(IV)X_6$	Cs <sub>2</sub> Snl <sub>6</sub>	Stable, suitable <i>E</i> g	Defect
$A_3B(III)_2X_9$	Cs <sub>3</sub> Bi <sub>2</sub> I <sub>9</sub>	Stable	Wide <i>E</i> g, defect
A <sub>2</sub> B(I)B(III)X <sub>6</sub>	Cs <sub>2</sub> AgBiBr <sub>6</sub>	Stable	Wide <i>E</i> g
$A_aB(III)_bX_{a+3b}$	Ag₃Bil <sub>6</sub>	High absorption	Phase separation, defect

Table 2.	Tuning	$E_{\rm a}$ of	double	perovskites.
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Precursor	Method	Product	E <sub>g</sub> (eV)	Feature	Ref.
Cs <sub>2</sub> AgBiBr <sub>6</sub>	A	$Cs_2(Ag_{1-a}Bi_{1-b})TI_xBr_6 (x = a+b)$	1.40–1.95	Toxicity of TI	[9]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	A	$Cs_2(Ag_{1-(2a+b)}Sn_a(II))(Bi_{1-b}Sn_b(IV))Br_6$	1.48 (i) and 1.71 (d)	Unstable Sn <sup>2+</sup>	[ <mark>10</mark> ]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	A	Cs <sub>2</sub> Ag(Bi <sub>1-x</sub> M <sub>x</sub> )Br <sub>6</sub> (M:In,Sb)	1.86 (Sb <sub>0.375</sub> ) –2.28 (In <sub>0.75</sub> )	Sb <sup>3+</sup> decreases while $In^{3+}$ increases $E_g$	[11]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	A	Cs <sub>2</sub> (Ag:Cu <sup>+</sup> /Cu <sup>2+</sup> )BiBr <sub>6</sub>	Tailing to 860 nm	Defect absorption	[14]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	A	Cs <sub>2</sub> Ag(BiFe)Br <sub>6</sub>	Tailing to 800 nm	Defect absorption	[15]
Cs <sub>2</sub> AgInCl <sub>6</sub>	A	Cs <sub>2</sub> AgIn <sub>1-x</sub> Fe <sub>x</sub> Cl <sub>6</sub>	1.6–2.8	For single crystal	[ <mark>16</mark> ]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	B (temperature)	Cs <sub>2</sub> AgBiBr <sub>6</sub>	Reversible		[ <mark>18</mark> ]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	B (temperature)	Cs <sub>2</sub> AgBiBr <sub>6</sub>	1.72–1.98	For single crystal	[ <b>19</b> ]
Cs <sub>2</sub> AgBiBr <sub>6</sub>	B (pressure)	Cs <sub>2</sub> AgBiBr <sub>6</sub>	1.70 @15 GPa	Partially retainable	[20]

A: Chemical composition. B: Physical structure.



Fig. 1. (Color online) Tuning  $E_q$  of double perovskites.

 $Bi^{3+}$  was completely disordered, the  $E_{q}$  could be reduced to 0.44 eV<sup>[17]</sup>. Gao et al.<sup>[18]</sup> reported that through thermallyinduced defects, as the temperature increased, the color of Cs<sub>2</sub>AgBiBr<sub>6</sub> single crystal and film can change from red to black, the  $E_{\alpha}$  decreased, but the original color of the film recovered after cooling. The finite-temperature molecular dynamics simulations indicated the synergistic effect of the incongruous bond lengths ( $R_{Aq-Br}$  and  $R_{Bi-Br}$ ) fluctuations and the related electron-phonon coupling, as well as the special spinorbit coupling effect, were the cause for the thermochromism. Gao et al.<sup>[19]</sup> increased the disorder degree of [Ag-Br<sub>6</sub>] and [BiBr<sub>6</sub>] octahedral by adjusting the crystallization speed of Cs<sub>2</sub>AgBiBr<sub>6</sub>. As the temperature increases, the disorder degree gradually increases, the lattice shrinks, initially leading to the formation of isolated defect states in the forbidden band, and finally a series of defect states, and reduced  $E_{\alpha}$ (60 °C, 1.98 eV; 150 °C, 1.72 eV). And this reduced  $E_{\rm q}$  can keep stable at room temperature. Zou et al.[20] found that high pressure can also significantly reduce  $E_{q}$  of Cs<sub>2</sub>AgBiBr<sub>6</sub> single crystal. Under 15 GPa pressure, the  $E_q$  was reduced from 2.2 to 1.7 eV. When the pressure was released, the  $E_{\alpha}$  was relatively lower than that at atmospheric pressure.

In summary, for double perovskite  $Cs_2AgBiBr_6$ , the effect of A-site doping on  $E_g$  is not obvious, the stability of X-site doping is intractable, and only B-site doping can significantly tune  $E_q$ . Changing the order of Ag<sup>+</sup> and Bi<sup>3+</sup> in space is much effective for reducing  $E_g$  (Table 2). We need further study  $E_g$ -narrowing mechanism of double perovskites and find effective methods to realize it.

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### References

- Slavney A H, Hu T, Lindenberg A M, et al. A bismuth-halide double perovskite with long carrier recombination lifetime for photovoltaic applications. J Am Chem Soc, 2016, 7, 2138
- [2] Wu C, Zhang Q, Liu Y, et al. The dawn of lead-free perovskite solar cell: Highly stable double perovskite Cs<sub>2</sub>AgBiBr<sub>6</sub> film. Adv Sci, 2018, 5, 1700759
- [3] Wang B, Li N, Wang X F, et al. Chlorophyll derivative-sensitized TiO<sub>2</sub> electron transport layer for record efficiency of Cs<sub>2</sub>AgBiBr<sub>6</sub> double perovskite solar cells. J Am Chem Soc, 2021, 143, 2207
- [4] Keshavarz M, Debroye E, Hofkens J, et al. Tuning the structural and optoelectronic properties of Cs<sub>2</sub>AgBiBr<sub>6</sub> double-perovskite single crystals through alkali-metal substitution. Adv Mater, 2020, 32, 2001878
- [5] Zhang Z, Wu C, Wang D, et al. Improvement of Cs<sub>2</sub>AgBiBr<sub>6</sub> double perovskite solar cell by rubidium doping. Org Electron, 2019, 74, 204
- [6] Jana M K, Janke S M, Mitzi D B, et al. Direct-bandgap 2D silver-bismuth iodide double perovskite: The structure-directing influence of an oligothiophene spacer cation. J Am Chem Soc, 2019, 141, 7955
- [7] Creutz S E, Crites E N, Gamelin D R, et al. Colloidal nanocrystals of lead-free double-perovskite (elpasolite) semiconductors: Synthesis and anion exchange to access new materials. Nano Lett, 2018, 18, 1118
- [8] Zhang C, Gao L, Ma T, et al. Design of a novel and highly stable lead-free Cs<sub>2</sub>NaBil<sub>6</sub> double perovskite for photovoltaic applica-

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tion. Sustain Energy Fuels, 2018, 2, 2419

- [9] Slavney A H, Leppert L, Karunadasa H I, et al. Defect-induced band-edge reconstruction of a bismuth-halide double perovskite for visible-light absorption. J Am Chem Soc, 2017, 139, 5015
- [10] Lindquist K P, Mack S A, Karunadasa H I, et al. Tuning the bandgap of  $Cs_2AgBiBr_6$  through dilute tin alloying. Chem Sci, 2019, 10, 10620
- [11] Du K, Meng W, Mitzi D B, et al. Bandgap engineering of lead-free double perovskite Cs<sub>2</sub>AgBiBr<sub>6</sub> through trivalent metal alloying. Angew Chem Int Ed, 2017, 56, 8158
- [12] Zhao X, Yang J, Zhang L, et al. Design of lead-free inorganic halide perovskites for solar cells via cation-transmutation. J Am Chem Soc, 2017, 139, 2630
- [14] Ji F, Huang Y, Gao F, et al. Near-infrared light-responsive Cudoped Cs<sub>2</sub>AgBiBr<sub>6</sub>. Adv Funct Mater, 2020, 30, 2005521
- [15] Ning W, Bao J, Gao F, et al. Magnetizing lead-free halide double perovskites. Sci Adv, 2020, 6, eabb5381
- [16] Ji F, Wang F, Gao F, et al. The atomic-level structure of bandgap engineered double perovskite alloys Cs<sub>2</sub>AgIn<sub>1-x</sub>Fe<sub>x</sub>Cl<sub>6</sub>. Chem Sci, 2021, 12, 1730
- [17] Yang J, Zhang P, Wei S, et al. Band structure engineering of Cs<sub>2</sub>Ag-BiBr<sub>6</sub> perovskite through order-disordered transition: A first-principle study. J Phys Chem Lett, 2018, 9, 31
- [18] Ning W, Zhao X G, Gao F, et al. Thermochromic lead-free halide double perovskites. Adv Funct Mater, 2019, 29, 1807375
- [19] Ji F, Klarbring J, Gao F, et al. Lead-free halide double perovskite Cs<sub>2</sub>AgBiBr<sub>6</sub> with decreased band gap. Angew Chem Int Ed, 2020, 59, 15191
- [20] Li Q, Wang Y, Pan W, et al. High-pressure band-gap engineering in lead-free Cs<sub>2</sub>AgBiBr<sub>6</sub> double perovskite. Angew Chem Int Ed, 2017, 56, 15969



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